

Title (en)
METHOD AND ARRAY FOR PROCESSING CARRIER MATERIALS BY MEANS OF HEAVY ION RADIATION AND SUBSEQUENT ETCHING

Title (de)
VERFAHREN UND ANORDNUNG ZUR BEARBEITUNG VON TRÄGERMATERIAL DURCH SCHWERIONENBESTRAHLUNG UND NACHFOLGENDEN ÄTZPROZESS

Title (fr)
PROCEDE ET SYSTEME POUR TRAITER UN MATERIAU SUPPORT PAR IRRADIATION AUX IONS LOURDS ET GRAVURE SUCCESSIVE

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Application
EP 03783928 A 20030723

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Abstract (en)
[origin: WO2004015161A1] The invention relates to a method and an array for processing carrier materials by means of heavy ion radiation and subsequent etching, wherein the heavy ion radiation is carried out in such a way that a ray beam (1) of an energy-rich heavy ion radiation (1.1) incides on the surface (2) of a carrier material in at least two different angles. According to the invention, the fluence, the energy and the direction of incidence of the heavy ion rays (1.1) are selected in such a way that a maximum amount of intersecting or coinciding latent ion traces (3) and common numbers of incisions of the recesses (4) resulting from a chemical etching process following heavy ion radiation are obtained.

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Citation (search report)
See references of WO 2004015161A1

Citation (examination)
• US 4855049 A 19890808 - TOULEMONDE MARCEL [FR], et al
• US 4832997 A 19890523 - BALANZAT EMMANUEL [FR], et al

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